

### 80V - 80W DMOS AUDIO AMPLIFIER WITH MUTE/ST-BY

- VERY HIGH OPERATING VOLTAGE RANGE (±40V)
- DMOS POWER STAGE
- HIGH OUTPUT POWER (UP TO 80W MUSIC POWER)
- MUTING/STAND-BY FUNCTIONS
- NO SWITCH ON/OFF NOISE
- NO BOUCHEROT CELLS
- VERY LOW DISTORTION
- VERY LOW NOISE
- SHORT CIRCUIT PROTECTION
- THERMAL SHUTDOWN

### **DESCRIPTION**

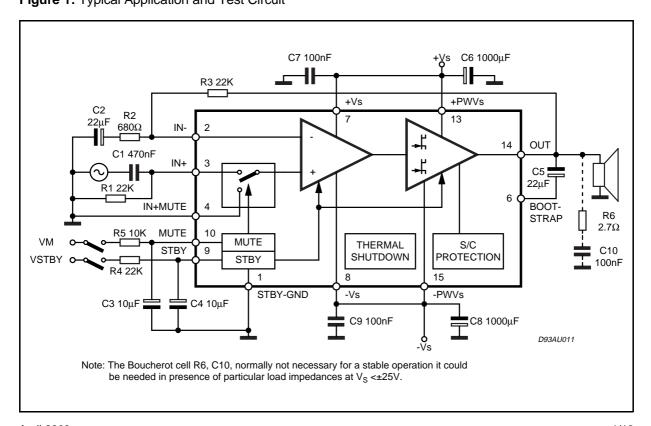
The TDA7295 is a monolithic integrated circuit in Multiwatt15 package, intended for use as audio class AB amplifier in Hi-Fi field applications (Home Stereo, self powered loudspeakers, Topclass TV). Thanks to the wide voltage range and

Figure 1: Typical Application and Test Circuit

# MULTIPOWER BCD TECHNOLOGY Multiwatt 15 ORDERING NUMBER: TDA7295

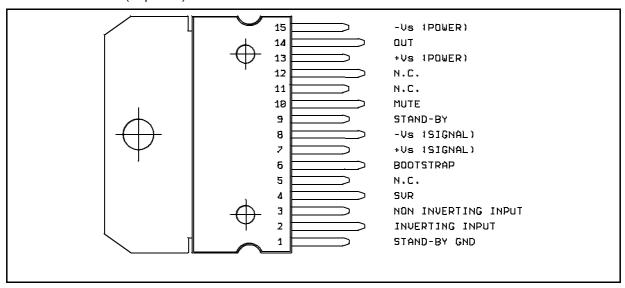
to the high out current capability it is able to supply the highest power into both  $4\Omega$  and  $8\Omega$  loads even in presence of poor supply regulation, with high Supply Voltage Rejection.

The built in muting function with turn on delay simplifies the remote operation avoiding switching on-off noises.

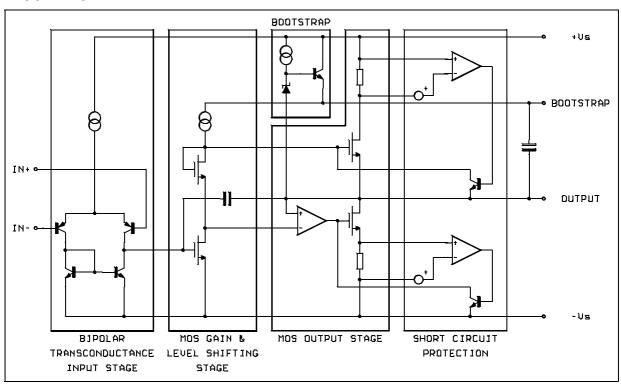


April 2003 1/13

### **PIN CONNECTION** (Top view)



### **BLOCK DIAGRAM**



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	±40	V
lo	Output Peak Current	6	Α
P <sub>tot</sub>	Power Dissipation T <sub>case</sub> = 70°C	50	W
T <sub>op</sub>	Operating Ambient Temperature Range	0 to 70	°C
T <sub>stg</sub> , T <sub>j</sub>	Storage and Junction Temperature	150	°C

### **THERMAL DATA**

Symbol Description				Unit
R <sub>th j-case</sub>	Thermal Resistance Junction-case	Max	1.5	°C/W

**ELECTRICAL CHARACTERISTICS** (Refer to the Test Circuit  $V_S = \pm 30V$ ,  $R_L = 8\Omega$ ,  $G_V = 30dB$ ;  $R_g = 50~\Omega$ ;  $T_{amb} = 25^{\circ}C$ , f = 1~kHz; unless otherwise specified.

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit	
Vs	Operating Supply Range		±10		±40	V	
Iq	Quiescent Current		20	30	65	mA	
I <sub>b</sub>	Input Bias Current				500	nA	
Vos	Input Offset Voltage				<u>+</u> 10	mV	
Ios	Input Offset Current				<u>+</u> 100	nA	
Po	RMS Continuous Output Power	$\begin{array}{l} d = 0.5\%: \\ V_S = \pm \ 30 \text{V}, \ R_L = 8 \Omega \\ V_S = \pm \ 26 \text{V}, \ R_L = 6 \Omega \\ \varsigma_S = \pm \ 22 \text{V}, \ R_L = 4 \Omega \end{array}$	45 45 45	50 50 50		W W W	
	Music Power (RMS) (*) $\Delta t = 1s$	$ \begin{array}{l} d = 10\%; \\ R_L = 8\Omega \; ; \; V_S = \pm 34V \\ (^{***}) \; R_L = 4\Omega; \; \; V_S = \pm 26V \end{array} $		80 80		W W	
d	Total Harmonic Distortion (**)	$P_O = 5W$ ; f = 1kHz $P_O = 0.1$ to 30W; f = 20Hz to 20kHz		0.005	0.1	% %	
		$V_S = \pm 22V, R_L = 4\Omega$ : $P_O = 5W; f = 1kHz$ $P_O = 0.1$ to 30W; f = 20Hz to 20kHz		0.01	0.1	% %	
SR	Slew Rate		7	10		V/μs	
$G_V$	Open Loop Voltage Gain			80		dB	
$G_V$	Closed Loop Voltage Gain		24	30	40	dB	
e <sub>N</sub>	Total Input Noise	A = curve f = 20Hz to 20kHz		1 2	5	μV μV	
fL, fH	Frequency Response (-3dB) P <sub>O</sub> = 1W 20Hz to 20kHz						
R <sub>i</sub>	Input Resistance		100			kΩ	
SVR	Supply Voltage Rejection	$f = 100Hz; V_{ripple} = 0.5Vrms$	60	75		dB	
Ts	Thermal Shutdown			145		°C	
STAND-B	Y FUNCTION (Ref: -V <sub>S</sub> or GND)						
V <sub>ST on</sub>	Stand-by on Threshold				1.5	V	
V <sub>ST off</sub>	Stand-by off Threshold		3.5			V	
ATT <sub>st-by</sub>	Stand-by Attenuation		70	90		dB	
I <sub>q st-by</sub>	Quiescent Current @ Stand-by			1	3	mA	
MUTE FUNCTION (Ref: -V <sub>S</sub> or GND)							
$V_{Mon}$	Mute on Threshold				1.5	V	
$V_{Moff}$	Mute off Threshold		3.5			V	
ATT <sub>mute</sub>	Mute Attenuation		60	80		dB	

Note (\*):

MUSIC POWER is the maximal power which the amplifier is capable of producing across the rated load resistance (regardless of non linearity)

1 sec after the application of a sinusoidal input signal of frequency 1KHz.

Note (\*\*): Tested with optimized Application Board (see fig. 2)

Note (\*\*\*): Limited by the max. allowable out current



OUT PGND VS PGND СОМ MUTE STBY SW2 SWI C6 -VS GND +VS TDA7295 

Figure 2: P.C.B. and components layout of the circuit of figure 1. (1:1 scale)

### Note

The Stand-by and Mute functions can be referred either to GND or -VS. On the P.C.B. is possible to set both the configuration through the jumper J1.

4

### APPLICATION SUGGESTIONS (see Test and Application Circuits of the Fig. 1)

The recommended values of the external components are those shown on the application circuit of Figure 1. Different values can be used; the following table can help the designer.

COMPONENTS	SUGGESTED VALUE	PURPOSE	LARGER THAN SUGGESTED	SMALLER THAN SUGGESTED
R1 (*)	22k	INPUT RESISTANCE	INCREASE INPUT IMPRDANCE	DECREASE INPUT IMPEDANCE
R2	680Ω	CLOSED LOOP GAIN	DECREASE OF GAIN	INCREASE OF GAIN
R3 (*)	22k	SET TO 30dB (**)	INCREASE OF GAIN	DECREASE OF GAIN
R4	22k	ST-BY TIME CONSTANT	LARGER ST-BY ON/OFF TIME	SMALLER ST-BY ON/OFF TIME; POP NOISE
R5	10k	MUTE TIME CONSTANT	LARGER MUTE ON/OFF TIME	SMALLER MUTE ON/OFF TIME
C1	0.47μF	INPUT DC DECOUPLING		HIGHER LOW FREQUENCY CUTOFF
C2	22μF	FEEDBACK DC DECOUPLING		HIGHER LOW FREQUENCY CUTOFF
C3	10μF	MUTE TIME CONSTANT	LARGER MUTE ON/OFF TIME	SMALLER MUTE ON/OFF TIME
C4	10μF	ST-BY TIME CONSTANT	LARGER ST-BY ON/OFF TIME	SMALLER ST-BY ON/OFF TIME; POP NOISE
C5	22μF	BOOTSTRAPPING		SIGNAL DEGRADATION AT LOW FREQUENCY
C6, C8	1000μF	SUPPLY VOLTAGE BYPASS		DANGER OF OSCILLATION
C7, C9	0.1μF	SUPPLY VOLTAGE BYPASS		DANGER OF OSCILLATION

<sup>(\*)</sup> R1 = R3 FOR POP OPTIMIZATION

<sup>(\*\*)</sup> CLOSED LOOP GAIN HAS TO BE  $\geq$  24dB

### **TYPICAL CHARACTERISTICS**

(Application Circuit of fig 1 unless otherwise specified)

Figure 3: Output Power vs. Supply Voltage.

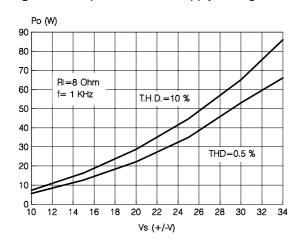


Figure 5: Output Power vs. Supply Voltage

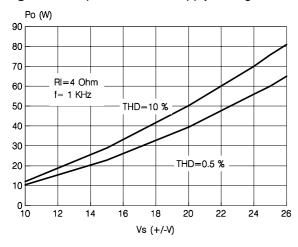


Figure 7: Distortion vs. Frequency

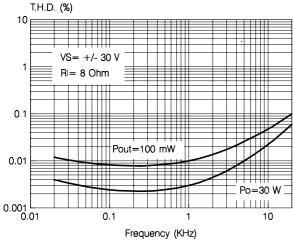


Figure 4: Distortion vs. Output Power

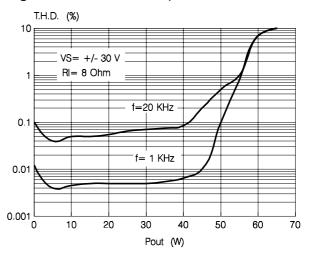


Figure 6: Distortion vs. Output Power

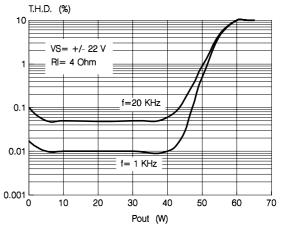
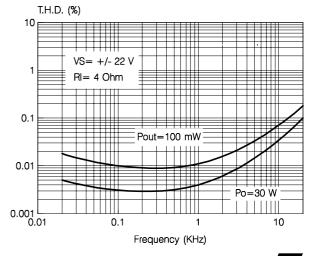


Figure 8: Distortion vs. Frequency



### **TYPICAL CHARACTERISTICS** (continued)

Figure 9: Quiescent Current vs. Supply Voltage

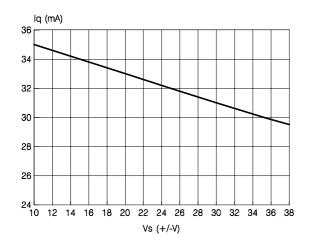


Figure 11: Mute Attenuation vs. V<sub>pin10</sub>

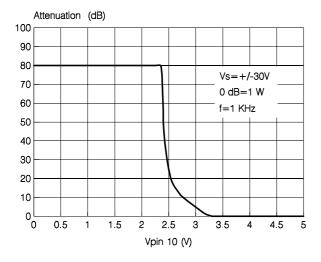


Figure 13: Power Dissipation vs. Output Power

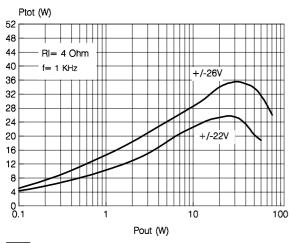


Figure 10: Supply Voltage Rejection vs. Frequency

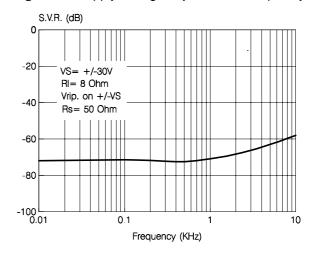


Figure 12: St-by Attenuation vs. V<sub>pin9</sub>

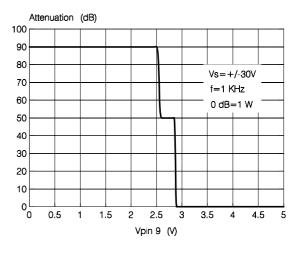
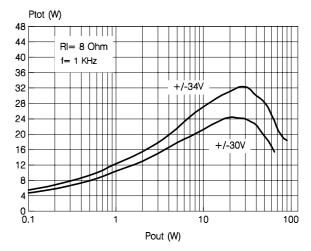


Figure 14: Power Dissipation vs. Output Power



57

### INTRODUCTION

In consumer electronics, an increasing demand has arisen for very high power monolithic audio amplifiers able to match, with a low cost the performance obtained from the best discrete designs.

The task of realizing this linear integrated circuit in conventional bipolar technology is made extremely difficult by the occurence of 2nd breakdown phenomenon. It limits the safe operating area (SOA) of the power devices, and as a consequence, the maximum attainable output power, especially in presence of highly reactive loads.

Moreover, full exploitation of the SOA translates into a substantial increase in circuit and layout complexity due to the need for sophisticated protection circuits.

To overcome these substantial drawbacks, the use of power MOS devices, which are immune from secondary breakdown is highly desirable.

The device described has therefore been developed in a mixed bipolar-MOS high voltage technology called BCD 100.

### 1) Output Stage

The main design task one is confronted with while developing an integrated circuit as a power operational amplifier, independently of the technology used, is that of realising the output stage.

The solution shown as a principle schematic by Fig 15 represents the DMOS unity-gain output buffer of the TDA7295.

This large-signal, high-power buffer must be capable of handling extremely high current and voltage levels while maintaining acceptably low har-

monic distortion and good behaviour over frequency response; moreover, an accurate control of quiescent current is required.

A local linearizing feedback, provided by differential amplifier A, is used to fullfil the above requirements, allowing a simple and effective quiescent current setting.

Proper biasing of the power output transistors alone is however not enough to guarantee the absence of crossover distortion.

While a linearization of the DC transfer characteristic of the stage is obtained, the dynamic behaviour of the system must be taken into account.

A significant aid in keeping the distortion contributed by the final stage as low as possible is provided by the compensation scheme, which exploits the direct connection of the Miller capacitor at the amplifier's output to introduce a local AC feedback path enclosing the output stage itself.

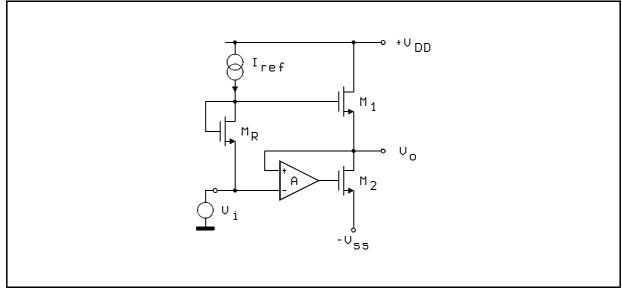
### 2) Protections

In designing a power IC, particular attention must be reserved to the circuits devoted to protection of the device from short circuit or overload conditions.

Due to the absence of the 2nd breakdown phenomenon, the SOA of the power DMOS transistors is delimited only by a maximum dissipation curve dependent on the duration of the applied stimulus.

In order to fully exploit the capabilities of the power transistors, the protection scheme implemented in this device combines a conventional SOA protection circuit with a novel local temperature sensing technique which "dynamically" controls the maximum dissipation.

Figure 15: Principle Schematic of a DMOS unity-gain buffer.



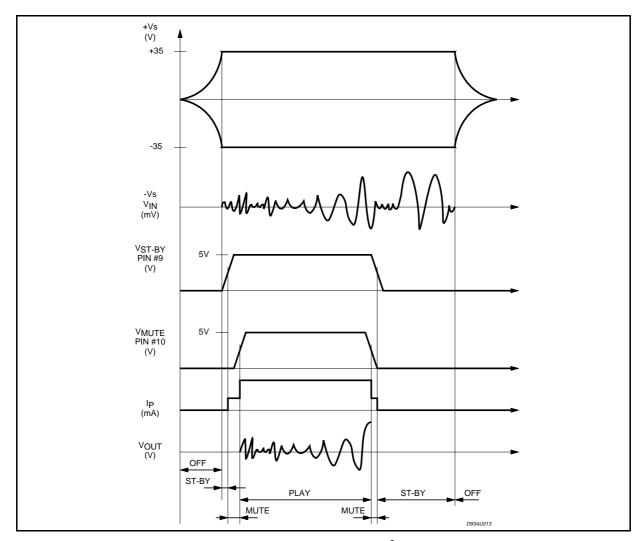
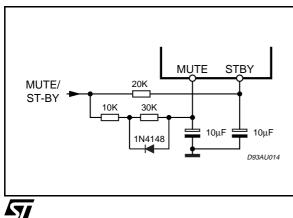


Figure 16: Turn ON/OFF Suggested Sequence

In addition to the overload protection described above, the device features a thermal shutdown circuit which initially puts the device into a muting state (@ Tj = 145  $^{\circ}$ C) and then into stand-by (@

Figure 17: Single Signal ST-BY/MUTE Control Circuit



 $Tj = 150 \, {}^{\circ}C$ ).

Full protection against electrostatic discharges on every pin is included.

### 3) Other Features

The device is provided with both stand-by and mute functions, independently driven by two CMOS logic compatible input pins.

The circuits dedicated to the switching on and off of the amplifier have been carefully optimized to avoid any kind of uncontrolled audible transient at the output.

The sequence that we recommend during the ON/OFF transients is shown by Figure 16.

The application of figure 17 shows the possibility of using only one command for both st-by and mute functions. On both the pins, the maximum applicable range corresponds to the operating supply voltage.

### **BRIDGE APPLICATION**

Another application suggestion is the BRIDGE configuration, where two TDA7295 are used, as shown by the schematic diagram of figure 25.

In this application, the value of the load must not be lower than 8 Ohm for dissipation and current capability reasons.

A suitable field of application includes HI-FI/TV subwoofers realisations.

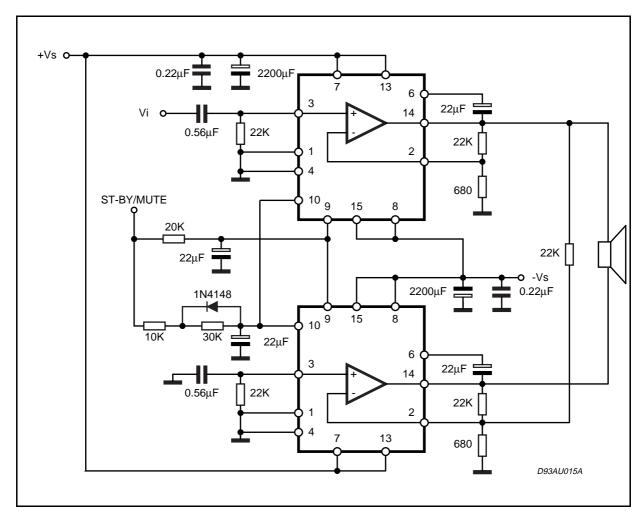
The main advantages offered by this solution are:

- High power performances with limited supply voltage level.
- Considerably high output power even with high load values (i.e. 16 Ohm).

The characteristics shown by figures 20 and 21, measured with loads respectively 8 Ohm and 16 Ohm.

With RI= 8 Ohm, Vs =  $\pm 22$ V the maximum output power obtainable is 100W, while with RI=16 Ohm, Vs =  $\pm 30$ V the maximum Pout is 100W.

Figure 18: Bridge Application Circuit



5

Figure 19: Frequency Response of the Bridge Application

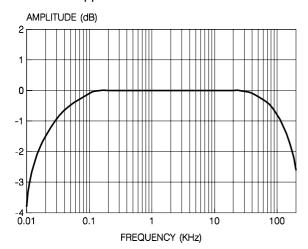


Figure 21: Distortion vs. Output Power

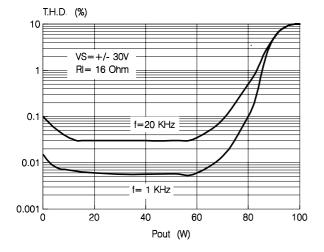
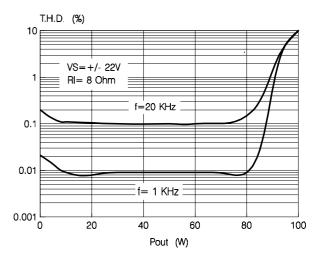
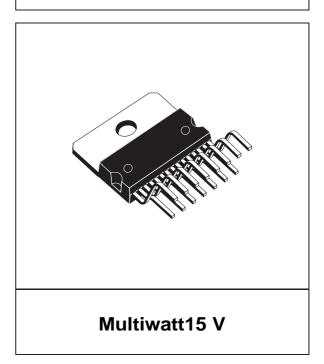


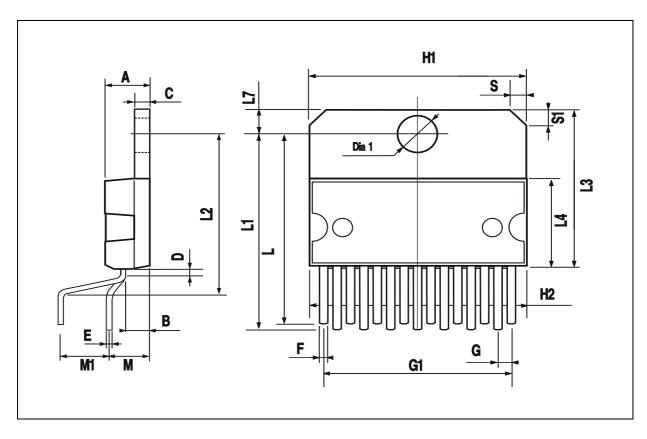
Figure 20: Distortion vs. Output Power



DIM	mm			inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			5			0.197	
В			2.65			0.104	
С			1.6			0.063	
D		1			0.039		
Е	0.49		0.55	0.019		0.022	
F	0.66		0.75	0.026		0.030	
G	1.02	1.27	1.52	0.040	0.050	0.060	
G1	17.53	17.78	18.03	0.690	0.700	0.710	
H1	19.6			0.772			
H2			20.2			0.795	
L	21.9	22.2	22.5	0.862	0.874	0.886	
L1	21.7	22.1	22.5	0.854	0.870	0.886	
L2	17.65		18.1	0.695		0.713	
L3	17.25	17.5	17.75	0.679	0.689	0.699	
L4	10.3	10.7	10.9	0.406	0.421	0.429	
L7	2.65		2.9	0.104		0.114	
М	4.25	4.55	4.85	0.167	0.179	0.191	
M1	4.63	5.08	5.53	0.182	0.200	0.218	
S	1.9		2.6	0.075		0.102	
S1	1.9		2.6	0.075		0.102	
Dia1	3.65		3.85	0.144		0.152	

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